



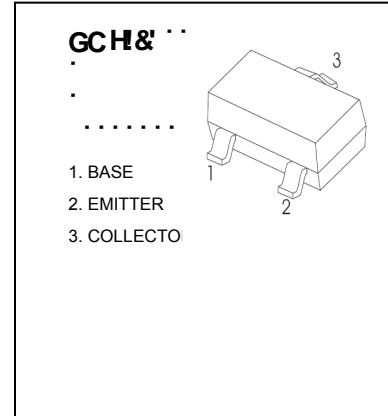
9 @ 7 HF CB 7 G H 9 7 < BC @ ; M 7 C ' Z @ 8

GCH& ' D`UghjW9 bWUdgi `UhY`Hf Ubgjghc f g`

.....67, %± TRANSISTOR (NPN)

: 95HI F9G`

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC807 (PNP)



A5L-AI A`F5HB; G`fh1&) °C`i b`Ygg`cH Yfk jgY`bchYX`

Gna Vc`	DUFUa YHf`	JUi Y`	I bjh`
J76c`	Collector-Base Voltage	50	V
J79c`	Collector-Emitter Voltage	45	V
J96c`	Emitter-Base Voltage	5	V
7`	Collector Current -Continuous	0.5	A
D7`	Collector Power Dissipation	0.3	W
H^	Junction Temperature	150	°C
H_glf`	Storage Temperature	-55-150	°C

9 @ 7 HF 7 5 @ 7 < 5 F 5 7 H 9 F -GH 7 G`fh1&) °C`i b`Ygg`cH Yfk jgY`gdYWjZYX`

DUFUa YHf`	Gna Vc`	HYgh V`bX]hcbg`	A in	Typ`	A ax	Unit
7 c`YWcf!VUgY VfYU_Xck b`j c`Hj Y`	V _{CB0}	I _C = 10μA, I _E =0	50			V
7 c`YWcf!Ya]Hf`VfYU_Xck b`j c`Hj Y`	V _{CE0}	I _C = 10mA, I _B =0	45			V
9 a]Hf`!VUgY VfYU_Xck b`j c`Hj Y`	V _{EBO}	I _E = 1μA, I _C =0	5			V
7 c`YWcf`W HcZZW ffYbh`	I _{CB0}	V _{CB} = 45 V, I _E =0			0.1	μA
9 a]Hf`W HcZZW ffYbh`	I _{EBO}	V _{EB} = 4V, I _C =0			0.1	μA
8 7`W ffYbh[Ujb`	h _{FE(1)}	V _{CE} = 1V, I _C = 100mA	100		600	
	h _{FE(2)}	V _{CE} = 1V, I _C = 500mA	40			
7 c`YWcf!Ya]Hf`gUhi fUjcb`j c`Hj Y`	V _{CE(sat)}	I _C = 500mA, I _B = 50mA			0.7	V
6 UgY!Ya]Hf`gUhi fUjcb`j c`Hj Y`	V _{BE(sat)}	I _C = 500mA, I _B = 50mA			1.2	V
6 UgY!Ya]Hf`j c`Hj Y`	V _{BE}	V _{CE} = 1 V, I _C = 500mA			1.2	V
7 c`YWyf`WUdUWjUbW`	C _{ob}	V _{CB} =10V, f=1MHz		10		pF
HfUbg]hcb`Z`Yei YbWni`	f _T	V _{CE} = 5 V, I _C = 10mA f=100MHz	100			MHz

7 @ GG= 7 5 HCB`C: `hFE`f`

FUb`	67, %±!%`	67, %±!&`	67, %±!(\$`
FUb[Y`	%%\$!&) \$`	% \$!(\$\$`	&) \$!* \$\$\$`
AUf_]b[`	* 5`	* 6`	* 7`

Typical Characteristics

BC817

